Revision. 5

MOS FET

FK3P02110L

Panasonic

FK3P02110L

Silicon N-channel MOSFET

For Load-switching

■ Features

- Low drain-source ON resistance:RDS(on)typ. = $12.5m\Omega$ (VGS = 2.5 V)
- · High heat dissipated and ultra-compact package PMCP
- RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: A1

■ Packaging

Embossed type (Thermo-compression sealing): 7 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Syllibol	Raung	UTIIL	
Drain-source voltage		VDS	24	V	
Gate-source voltage		VGS	±12	V	
Drain current	Ta = 25 °C, DC *2	ID1	3.0	A	
Diam current	Ta = 25 °C, DC *3	ID2	6.0	A	
Drain current	Ta = 25 °C *1 *2	IDp1	9.0	A	
(Pulsed)	Ta = 25 °C *1 *3	IDp2	18.0		
Total power	Ta = 25 °C, DC *2	PD1	200	mW	
dissipation	Ta = 25 °C, DC *3	PD2	750	IIIVV	
Channel temperature		Tch	150		
Operating ambient temperature		Topr	-40 to +85	°C	
Storage temperature range		Tstg	-55 to +150		
	D / O / /0/				

Note : *1 $t = 10 \mu s$, Duty Cycle < 1%

- *2 When mounted on glass epoxy board typeA (Refer to Figure1)
- *3 When mounted on glass epoxy board typeB (Refer to Figure2)

■ Electrical Characteristics Ta = 25 °C ±3 °C Static Characteristics

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Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source breakdown voltage	VDSS	ID = 1.0 mA, VGS = 0 V	24			V
Zero gate voltage drain current	IDSS	VDS = 24 V, VGS = 0 V			1.0	μΑ
Gate-source leakage current	IGSS	VGS = ±8 V, VDS = 0 V			±10	μΑ
Gate-source threshold voltage	Vth	ID = 1.0 mA, VDS = 10 V	0.4	0.85	1.4	V
Drain-source on-state resistance	RDS(on)	ID = 3.0 A, VGS = 2.5 V		12.5	20.0	mΩ

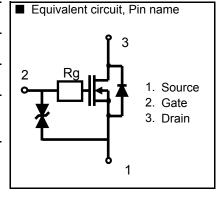
Dynamicic Characteristics

Established: 2012-10-25

: 2013-05-16

Revised

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input capacitance *1	Ciss			1500		
Output capacitance *1	Coss	VDS = 10 V, VGS = 0 V, f = 1 MHz		140		pF
Reverse transfer capacitance *1	Crss			140		



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Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Turn-on delay time *1 *2	td(on)	VDD = 10 V, VGS = 0 to 4 V,ID = 3.0 A		0.6		110
Rise time *1 *2	tr	VDD = 10 V, VGS = 0 t0 4 V,ID = 3.0 A		0.9		μs
Turn-off delay time *1 *2	td(off)	VDD = 10 V. VGS = 4 to 0 V.ID = 3.0 A		5.0		116
Fall time *1 *2	tf	VDD = 10 V, VGS = 4 t0 0 V,ID = 3.0 A		2.3		μs

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuringmethods for transistors.

- 2. *1 Assured by design
 - *2 Refer to figure3, measurement circuit for Turn-on delay time / Rise time / Turn-off delay time / Fall time

Figure1: Glass epoxy board typeA

Material:FR4, Size:25.4mm x 25.4mm x t 1.0mm, Cu pad:tickness 36 μm, 25.3mm²

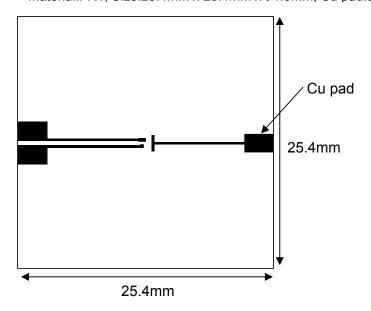
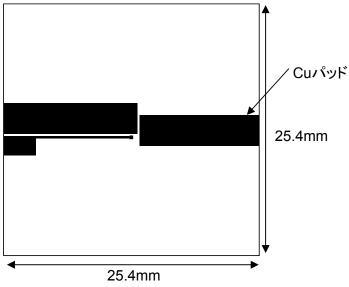


Figure2: Glass epoxy board typeB Material:FR4, Size:25.4mm x 25.4mm x t 1.0mm, Cu pad:tickness 36 μm, 82.0mm²

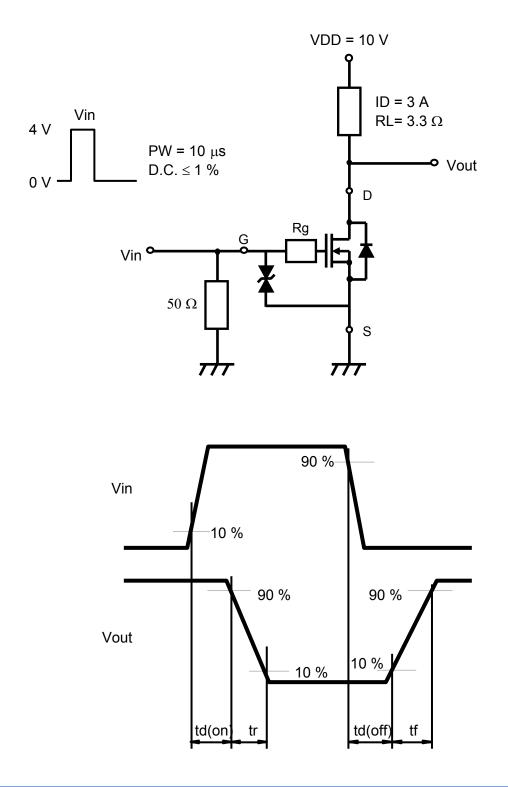


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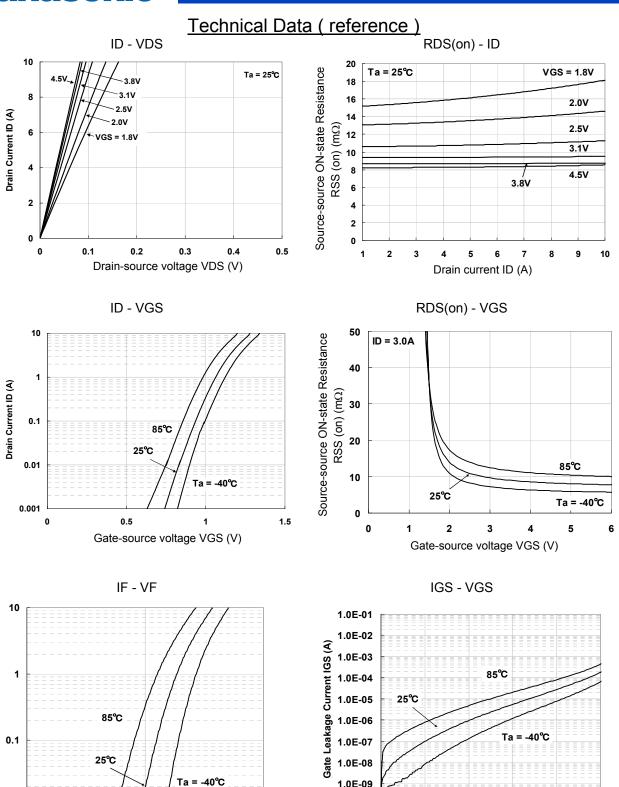
Figure3: Measurement circuit for Turn-on delay time / Rise time / Turn-off delay time / Fall time



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1.0E-09 1.0E-10

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Gate-source voltage VGS (V)

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0.5 Source-drain forward voltage VF (V)

Diode Foward Current IF (A)

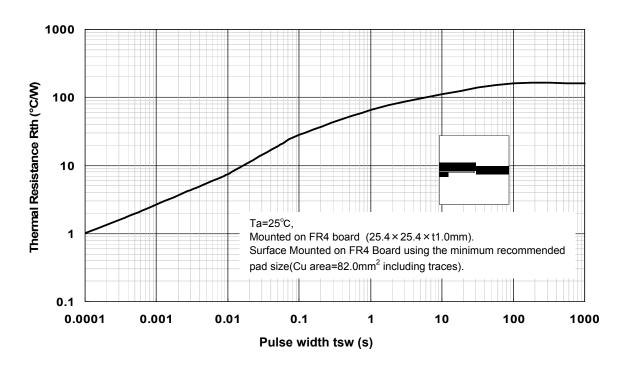
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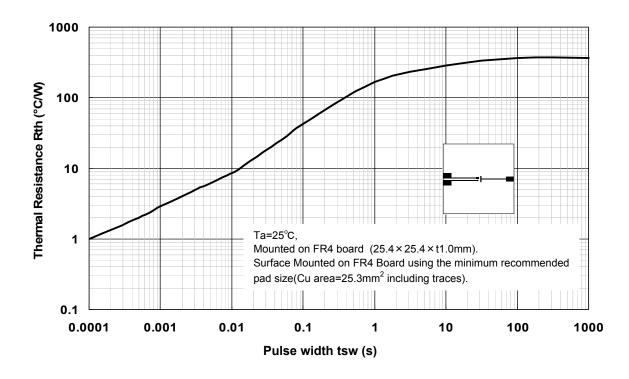
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<u>Technical Data (reference)</u> Rth - tsw



Rth - tsw



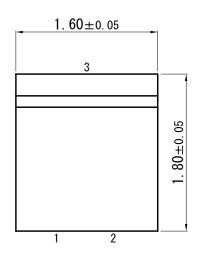
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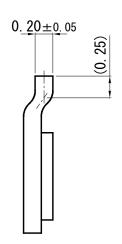
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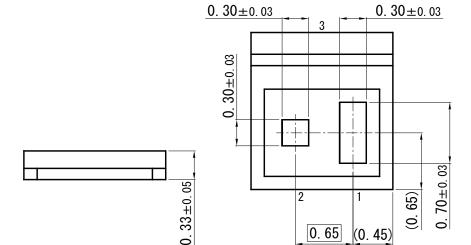
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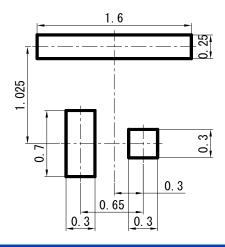








■ Land Pattern (Reference) (Unit: mm)



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